

CLAIM AMENDMENTS

1. (Currently Amended) An integrated circuit device comprising:
a semiconductor amplification element supplied with a voltage from a first power source; and
a bias circuit for applying a bias voltage to the semiconductor amplification element,
wherein

~~a power source of~~ the bias circuit is supplied with a second voltage from a second power source,

the second power source is connected to ~~a~~ the first power source of the semiconductor amplification element via a semiconductor element ~~such that, and~~
idle current of the semiconductor amplification element ~~is changed~~ changes in response to ~~a change of a supply~~ the voltage of supplied by the first power source to the semiconductor amplification element.

2. (Previously Presented) The integrated circuit device according to Claim 1, wherein the semiconductor element is a transistor.

3. (Previously Presented) The integrated circuit device according to Claim 1, wherein the semiconductor element is a diode.

4. (Currently Amended) The integrated circuit device according to Claim 1, which acts as a power amplifier circuit, including a transistor as the semiconductor amplification element, wherein the bias circuit includes a bias generating circuit for generating a base bias of the transistor and a temperature compensation circuit for temperature compensation of the bias generating circuit.